

What is claimed is:

1. A method of manufacturing semiconductor devices, comprising:  
forming an isolating film on a given region of a semiconductor substrate to  
5 define a first region and a second region;  
forming a first oxide film on the entire structure and then removing the first  
oxide film from the second region using a photoresist film pattern;  
removing the photoresist film pattern using a solvent;  
implementing an oxidization process to form a second oxide film on the  
10 semiconductor substrate in the second region;  
forming a polysilicon film on the entire structure and then patterning the  
polysilicon film to form gate electrodes in the first and second regions, respectively,  
and  
implementing an impurity ion implantation process to form junction regions at  
15 given regions on the semiconductor substrate.

2. The method as claimed in claim 1, wherein the first oxide film is  
formed thicker than the second oxide film.

20 3. The method as claimed in claim 1, wherein the photoresist film is  
formed using an i-line series photoresist material.

4. The method as claimed in claim 1, wherein the solvent includes any  
one of ethylcellsoluve acetate (ECA), methylamyl ketone (MAK), ethyl pyruvate  
25 (EP), ethyl lactate (EL), 3-methylmethoxy propionate (MMP),  
propyleneglycomonomethyl ether (PGME), propyleneglycol-monomethylether  
acetate (PGMEA) and ethoxyethyl propionate (EEP).

5. The method as claimed in claim 1, wherein the polysilicon film is  
30 formed without applying a vacuum and is formed using  $\text{SiH}_4$  gas or  $\text{Si}_2\text{H}_6$  gas at a  
temperature ranging from about  $580^\circ\text{C}$  to about  $630^\circ\text{C}$ .